# UTC UNISONIC TECHNOLOGIES CO., LTD

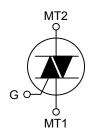
UT136F/G **Preliminary TRIAC** 

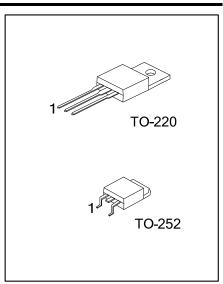
# TRIAC

#### DESCRIPTION

Passivated triac in a plastic envelope, suitable for surface mounting, intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial and domestic lighting, heating and static switching.

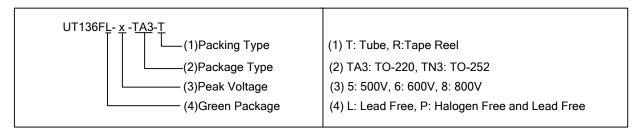
#### **SYMBOL**



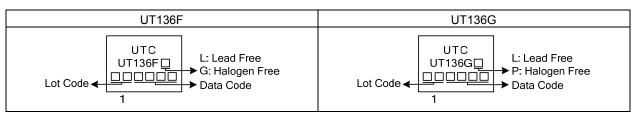


#### ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Deaking	
Lead Free	Halogen Free Package 1		1	2	3	Packing	
UT136FL-x-TA3-T	UT136FG-x-TA3-T	TO-220	MT1	MT2	G	Tube	
UT136FL-x-TN3-R	UT136FG-x-TN3-R	TO-252	MT1	MT2	G	Tape Reel	
UT136GL-x-TA3-T	UT136GP-x-TA3-T	TO-220	MT1	MT2	G	Tube	
UT136GL-x-TN3-R	UT136GP-x-TN3-R	TO-252	MT1	MT2	G	Tape Reel	



## **MARKING**



### ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT	
	UT136F/G-5		500 (Note 2)	
Repetitive Peak Off-State Voltages	UT136F/G-6	$V_{DRM}$	600 (Note 2)	V
	UT136F/G-8		800	
RMS On-State Current Full Sine Wave, Tmb	<sub>5</sub> ≤107°C	I <sub>T(RMS)</sub>	4	Α
Non-Repetitive Peak On-State Current t = 20ms			25	
(Full Sine Wave, T <sub>J</sub> =25°C Prior To Surge)	t = 16.7 ms	I <sub>TSM</sub>	27	A
I <sup>2</sup> t For Fusing (t =10ms)	l <sup>2</sup> t	3.1	A <sup>2</sup> s	
Describing Data Of Diag Of On Otata	T2+ G+		50	
Repetitive Rate Of Rise Of On-State	T2+ G-	di /dt	50	A /u.o
Current After Triggering $I_{TM}$ =6A, $I_{G}$ =0.2A, $d_{IG}/dt$ =0.2A/µs	T2- G-	dl <sub>⊤</sub> /dt	50	A/µs
u <sub> G</sub> /uι-υ.2Α/μδ	T2- G+		10	
Peak Gate Voltage		$V_{GM}$	5	V
Peak Gate Current	$I_{GM}$	2	Α	
Peak Gate Power	$P_{GM}$	5	W	
Average Gate Power (Over Any 20ms Perio	P <sub>G(AV)</sub>	0.5	W	
Junction Temperature	T <sub>J</sub>	125	°C	
Storage Temperature	T <sub>STG</sub>	-40 ~ +150	°C	

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

## ■ THERMAL DATA

PARAMETER		SYMBOL	RATINGS	UNIT	
Landing to Ambiguit	TO-220	0	60	12001	
Junction to Ambient	TO-252	$\theta_{JA}$	75	K/W	

## ■ STATIC CHARACTERISTICS (T<sub>J</sub> =25°C, unless otherwise specified)

DADAMETED	PARAMETER SYMBOL TEST CONDITIONS		MIN	TYP	MAX		UNIT		
PARAMETER	STIVIBOL	TEST CONDITIONS   WIII		IVIIIN	IIF	UT136F	UT136G	OINIT	
	I <sub>GT</sub>	V <sub>D</sub> =12V, I <sub>T</sub> =0.1A	T2+G+		5	25	50	mA	
Cata Trigger Current			T2+G-		8	25	50		
Gate Trigger Current			T2-G-		11	25	50		
			T2-G+		30	70	100		
Latching Current	lι	V <sub>D</sub> =12V, I <sub>GT</sub> =0.1A	T2+G+		7	20	30	mA	
			T2+G-		16	30	45		
			T2-G-		5	20	30		
			T2-G+		7	30	45		
Holding Current	l <sub>Η</sub>	V <sub>D</sub> =12V, I <sub>GT</sub> =0.1A			5	15	30	mA	
On-State Voltage	$V_{T}$	I <sub>T</sub> =5A			1.4	1.70		V	
Gate Trigger Voltage	$V_{GT}$	V <sub>D</sub> =12V, I <sub>T</sub> =0.1A			0.7	1.5		V	
		V <sub>D</sub> =400V, I <sub>T</sub> =0.1A, T <sub>J</sub> =125°C		0.25	0.4			V	
Off-State Leakage Current	$I_D$	$V_D = V_{DRM(max)}, T_J = 12$		0.1	0.5		mA		

<sup>2.</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the traic may switch to the on-state. The rate of rise of current should not exceed  $3A/\mu s$ .

# ■ **DYNAMIC CHARACTERISTICS** (T<sub>J</sub> =25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN		TVD	NANY	LINIT
PARAIVIETER	STIVIBUL	TEST CONDITIONS	UT136F	UT136G	TYP	IVIAA	UNIT
Critical Rate Of Rise Of Off-State Voltage		V <sub>DM</sub> =67% V <sub>DRM(max)</sub> , T <sub>J</sub> =125°C, exponential waveform, gate open circuit	50	200	250		V/µs
Critical Rate Of Change Of Commutating Voltage	dV <sub>com</sub> /dt	V <sub>DM</sub> =400V, T <sub>J</sub> =95°C, I <sub>T(RMS)</sub> =4A, dI <sub>com</sub> /dt=1.8A/ms, gate open circuit		10	50		V/µs
Gate Controlled Turn-On Time	I at	$I_{TM}$ =6A, $V_D$ = $V_{DRM(max)}$ , $I_G$ =0.1A, $dI_G$ / $dt$ =5A/ $\mu$ s			2		μs

TRIAC